Lonten N-channel 650V, 20A, 0.18Ω LonFET™ Power MOSFET

Description

LonFET™ Power MOSFET is fabricated using advanced super junction technology. The resulting device has extremely low on resistance, making it especially suitable for applications which require superior power density and outstanding efficiency.

Features

- Ultra low $R_{DS(on)}$
- Ultra low gate charge (typ. Q_g = 39nC)
- 100% UIS tested
- RoHS compliant

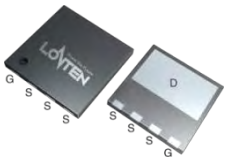
Applications

- Power factor correction (PFC).
- Switched mode power supplies (SMPS).
- Uninterruptible power supply (UPS).

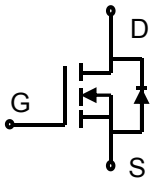
Product Summary

V_{DS} @ $T_{j,max}$	700V
$R_{DS(on),max}$	0.18Ω
I_{DM}	60A
$Q_{g,typ}$	39nC

Pin Configuration



DFN8×8



N-Channel MOSFET

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	650	V
Continuous drain current (T_C = 25°C)	I_D	20	A
(T_C = 100°C)		13	A
Pulsed drain current [1]	I_{DM}	60	A
Gate-Source voltage	V_{GSS}	±30	V
Avalanche energy, single pulse [2]	E_{AS}	600	mJ
Power Dissipation	P_D	108	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C
Continuous diode forward current	I_S	20	A
Diode pulse current	$I_{S,pulse}$	60	A

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.15	°C/W
Thermal Resistance, Junction-to-Ambient [3]	$R_{\theta JA}$	75	°C/W
Soldering temperature, wavesoldering only allowed at leads. (1.6mm from case for 10s)	T_{sold}	260	°C

Package Marking and Ordering Information

Device	Device Package	Marking	Units/Reel
LSNC65R180GT	DFN 8×8	LSNC65R180GT	3000

Electrical Characteristics

T_c = 25°C unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	V_{GS}=0 V, I_D=0.25 mA	650	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=0.25mA	2.5	3.5	4.5	V
Drain cut-off current	I_{DSS}	V_{DS}=650 V, V_{GS}=0 V,				μA
		T_j = 25°C	-	-	1	
		T_j = 125°C	-	10	-	
Gate leakage current, Forward	I_{GSSF}	V_{GS}=30 V, V_{DS}=0 V	-	-	100	nA
Gate leakage current, Reverse	I_{GSSR}	V_{GS}=-30 V, V_{DS}=0 V	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=10 A	-			
		T_j = 25°C	-	0.16	0.18	Ω
		T_j = 150°C	-	0.4	-	
Gate resistance	R_G	f=1 MHz, open drain	-	4.4	-	Ω
Dynamic characteristics						
Input capacitance	C_{iss}	V_{DS} = 25 V, V_{GS} = 0 V,	-	2637	-	
Output capacitance	C_{oss}	f = 1 MHz	-	1250	-	pF
Reverse transfer capacitance	C_{rss}		-	17	-	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 380V, I_D = 10A	-	23	-	
Rise time	t_r	R_G = 4.7Ω, V_{GS}=10V	-	33	-	ns
Turn-off delay time	$t_{d(off)}$		-	113	-	
Fall time	t_f		-	11	-	
Gate charge characteristics						
Gate to source charge	Q_{gs}	V_{DD}=480 V, I_D=10A,	-	10.3	-	
Gate to drain charge	Q_{gd}	V_{GS}=0 to 10 V	-	13.7	-	nC
Gate charge total	Q_g		-	39	-	
Gate plateau voltage	$V_{plateau}$		-	5.5	-	V
Reverse diode characteristics						
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=10A	-	-	1.2	V
Reverse recovery time	t_{rr}	V_R=50 V, I_F=20A,	-	345	-	ns
Reverse recovery charge	Q_{rr}	dI_F/dt=100 A/μs	-	3.8	-	μC
Peak reverse recovery current	I_{rrm}		-	22	-	A

Notes:

1. Limited by maximum junction temperature, maximum duty cycle is 0.75.

2. I_{AS} = 5A,L=48mH,V_{DD} =60V, Starting T_j= 25°C.

3. Weld the device to a PCB board with the size of 32mm*36mm and then place it in an one-cubic-foot air static box.

Electrical Characteristics Diagrams

Figure 1. On-Region Characteristics

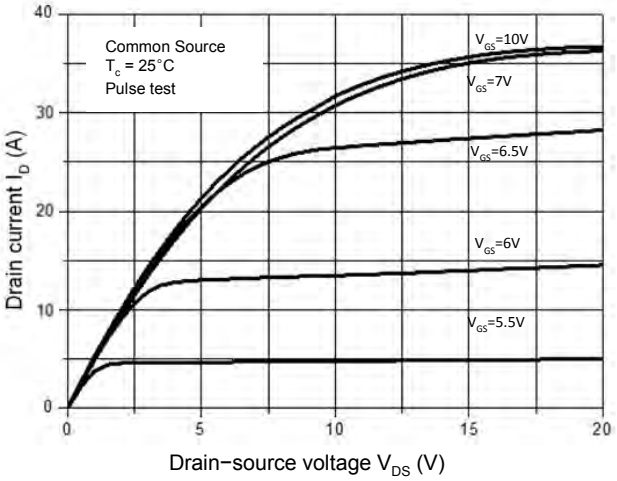


Figure 2. Transfer Characteristics

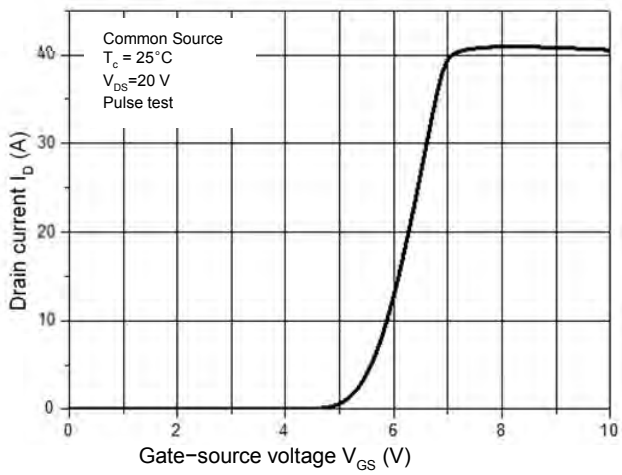


Figure 3. On-Resistance Variation vs. Drain Current

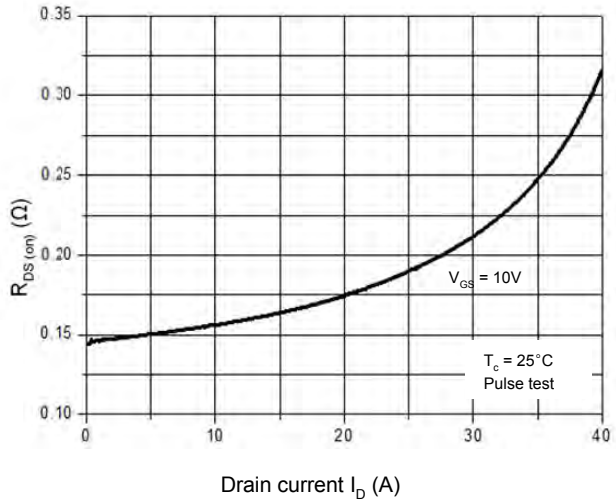


Figure 4. Threshold Voltage vs. Temperature

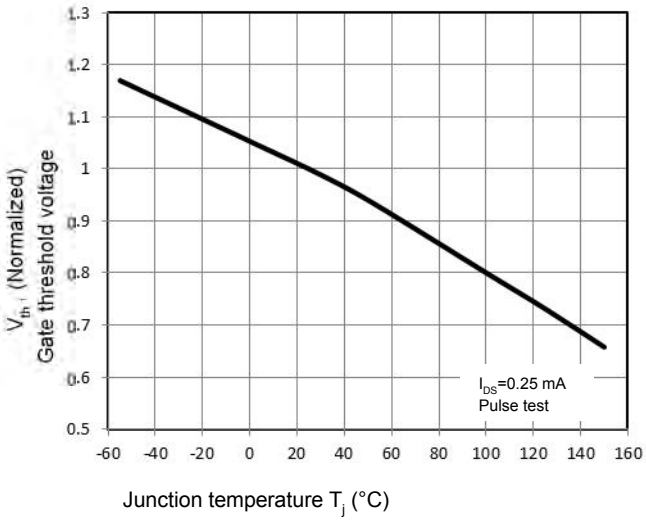


Figure 5. Breakdown Voltage vs. Temperature

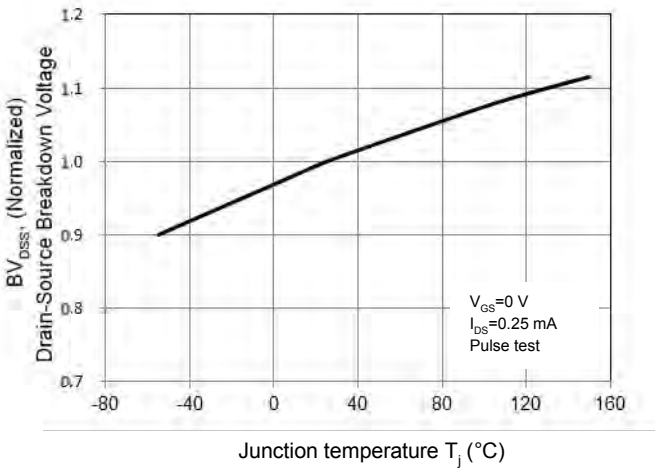


Figure 6. On-Resistance vs. Temperature

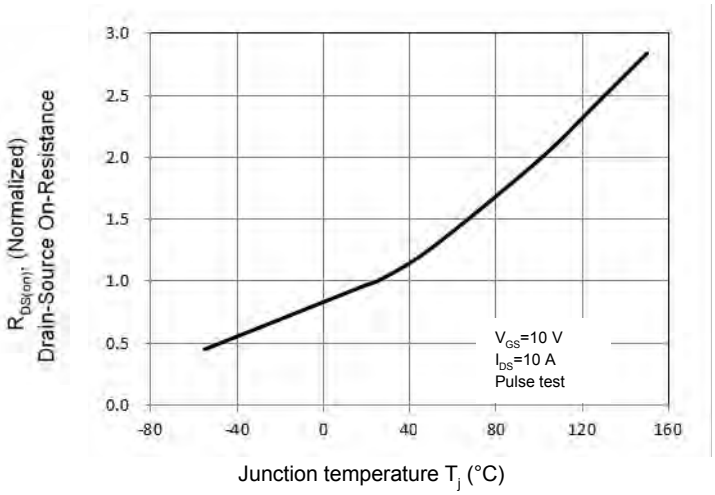


Figure 7. Capacitance Characteristics

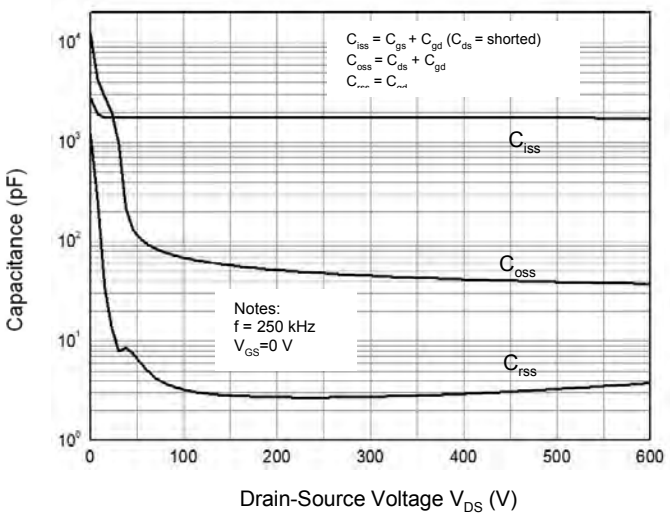


Figure 8. Gate Charge Characteristics

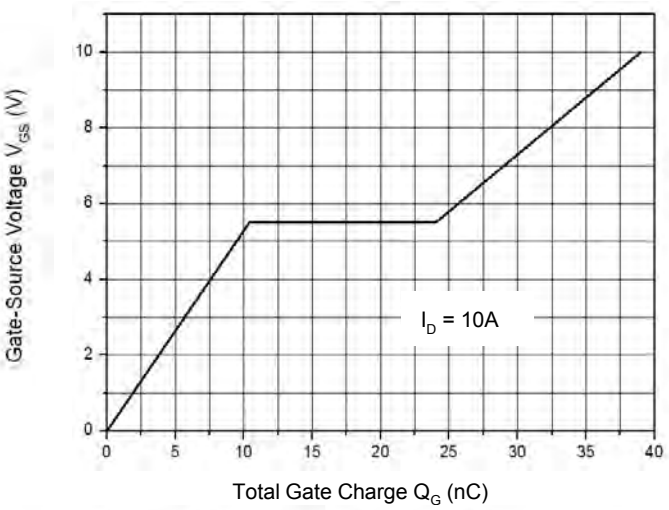


Figure 9.Power Dissipation vs.Temperature

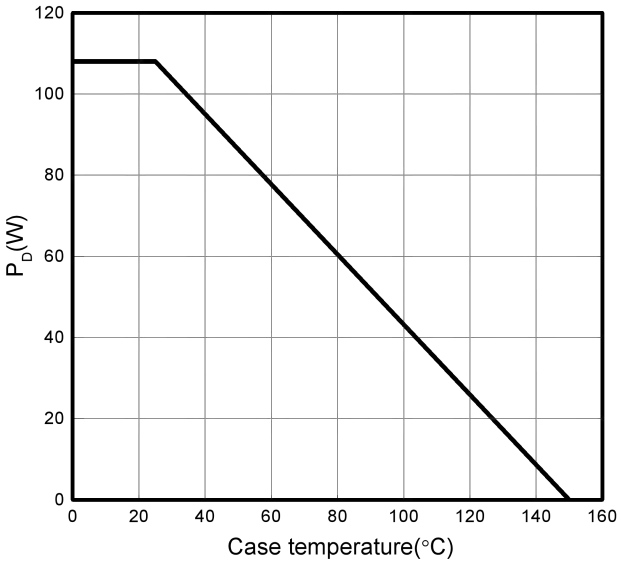


Figure 10: Safe Operating Area

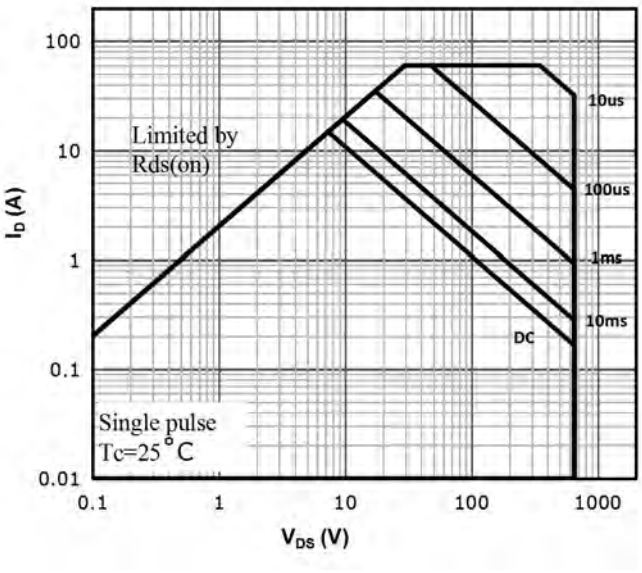
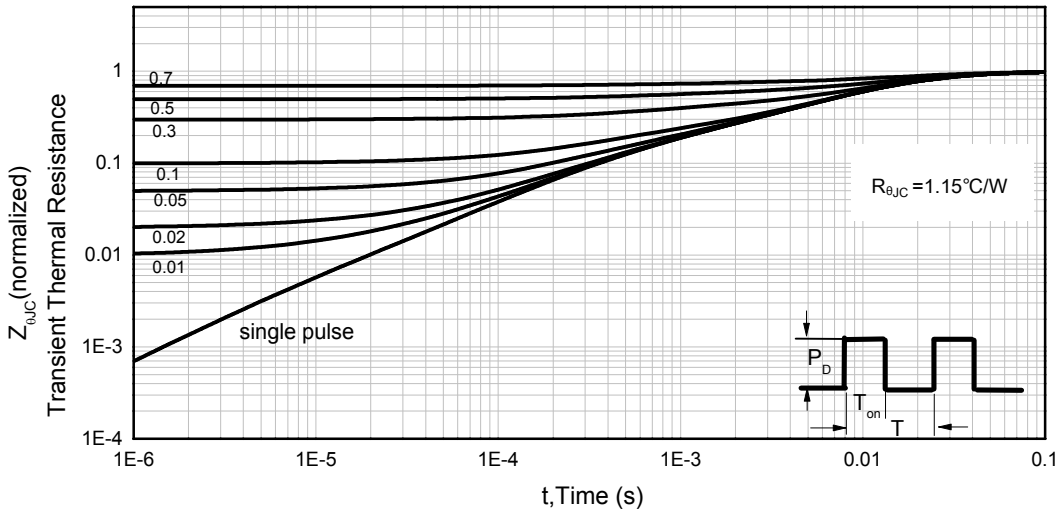
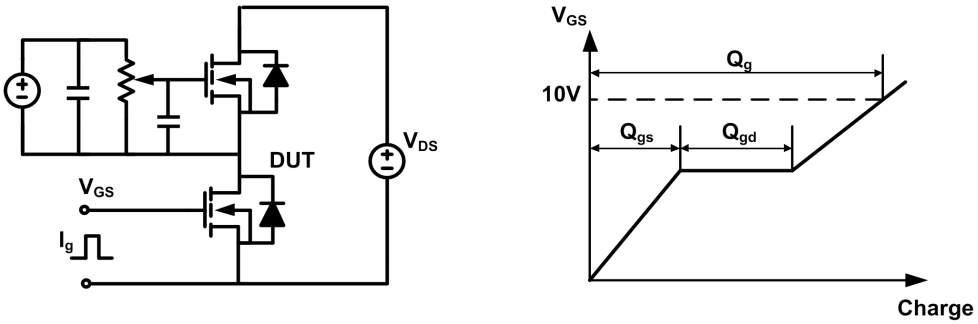


Figure 11. Normalized Maximum Transient Thermal Impedance (RthJC)

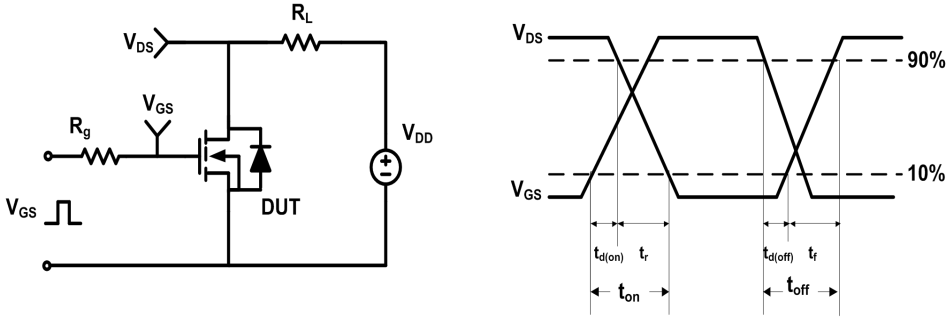


Test Circuit & Waveforms

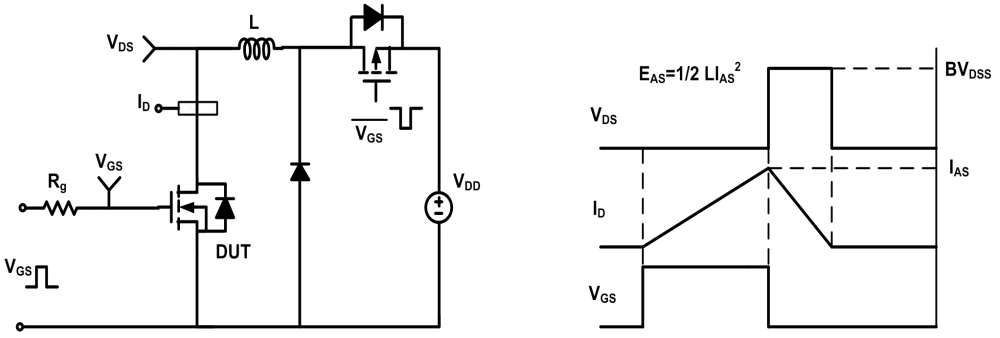
Gate Charge Test Circuit & Waveform



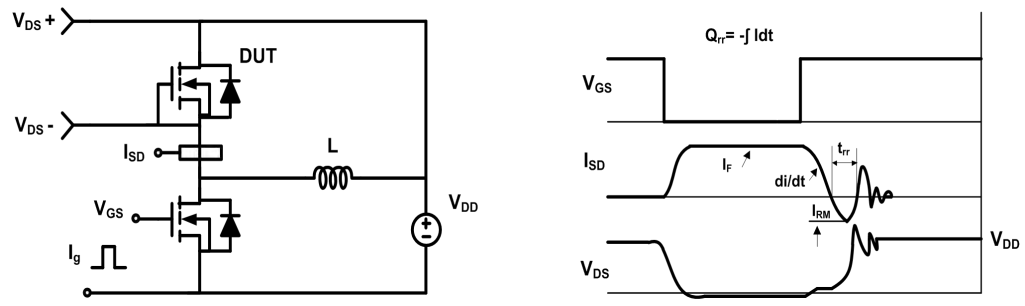
Resistive Switching Test Circuit & Waveform



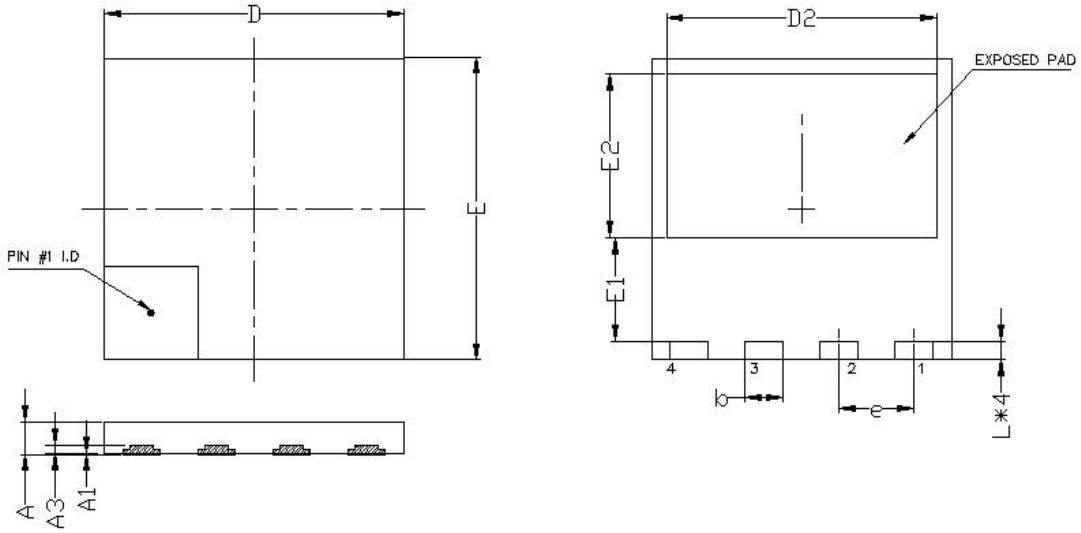
Unclamped Inductive Switching (UIS) Test Circuit & Waveform



Diode Recovery Test Circuit & Waveform



Mechanical Dimensions for DFN8×8



DIMENSIONS IN MILLITMETERS		
SYMBOL	MIN	MAX
A	0.75	1.00
A1	0.00	0.05
A3	0.10	0.30
b	0.90	1.10
D	7.90	8.10
E	7.90	8.10
D2	7.10	7.30
E1	2.65	2.85
E2	4.25	4.65
e	2.00BSC	
L	0.4	0.6